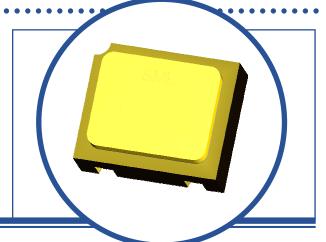
SILICON PLANAR EPITAXIAL PNP TRANSISTOR



2N2907ACSM

- Low Power, High Speed Saturated Switching
- Hermetic Surface Mounted Package.
- Ideally suited for High Speed Switching and General Purpose Applications
- Screening Options Available



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise stated)

VCBO	Collector – Base Voltage		-60V
VCEO	Collector – Emitter Voltage		-60V
V _{EBO}	Emitter – Base Voltage	-5V	
IC	Continuous Collector Current		-600mA
PD	Total Power Dissipation at T	д = 25°С	500mW
	De	erate Above 37.5°C	3.08mW/°C
Тј	Junction Temperature Range		-65 to +200°C
T _{stg}	Storage Temperature Range		-65 to +200°C

THERMAL PROPERTIES (Each Device)

Symbols	Parameters	Min.	Тур.	Max.	Units
R _{eja}	Thermal Resistance, Junction To Ambient			325	°C/W

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.





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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise stated)

Symbols	Parameters Collector-Emitter Breakdown Voltage	Test Conditions		Min.	Тур	Max.	Units
V _(BR) CEO ⁽¹⁾		I _C = -10mA	I _B = 0	-60			V
ICBO	Collector Cut-Off Current	V _{CB} = -60V	$I_{E} = 0$			-10	μA
		V _{CB} = -50V	I _E = 0			-10	nA
			T _A = 150°C			-10	μA
I _{EBO}	Emitter Cut-Off Current	V _{EB} = -5V	$I_{C} = 0$			-10	μA
		$V_{EB} = -4V$	I _C = 0			-50	nA
ICES	Collector Cut-Off Current	V _{CE} = -50V				-50	nA
V _{CE(sat}) ⁽¹⁾	Collector-Emitter Saturation Voltage	I _C = -150mA	I _B = -15mA			-0.4	V
		I _C = -500mA	I _B = -50mA			-1.6	
V _{BE(sat)} ⁽¹⁾	Base-Emitter Saturation Voltage	I _C = -150mA	I _B = -15mA	-0.6		-1.3	
		I _C = -500mA	I _B = -50mA			-2.6	
h _{FE} ⁽¹⁾	Forward-current transfer ratio	I _C = -0.1mA	$V_{CE} = -10V$	75			
		I _C = -1.0mA	$V_{CE} = -10V$	100		450	
		I _C = -10mA	V _{CE} = -10V	100			
			T _A = -55°C	50			
		I _C = -150mA	V _{CE} = -10V	100		300	
		I _C = -500mA	V _{CE} = -10V	50			

DYNAMIC CHARACTERISTICS

h _{fe}	Small signal forward-current transfer ratio	I _C = -20mA	V _{CE} = -20V	2			
		f = 100MHz		2			
h _{fe}	Small Signal Current Gain	I _C = -1.0mA	$V_{CE} = -10V$	100			
		f = 1.0KHz		100			
C _{obo}	Output Capacitance	V _{CB} = -10V	$I_{E} = 0$			8	pF
		f = 1.0MHz					
C _{ibo}	Input Capacitance	$V_{EB} = -2V$	$I_{C} = 0$			30	
		f = 1.0MHz				50	
^t on	Turn-On Time	I _C = -150mA	$V_{CC} = -30V$		45	45	
		I _{B1} = -15mA					ns
^t off	Turn-Off Time	I _C = -150mA	$V_{CC} = -30V$		300		
		I _{B1} = - I _{B2} = -15	mA			500	

Notes

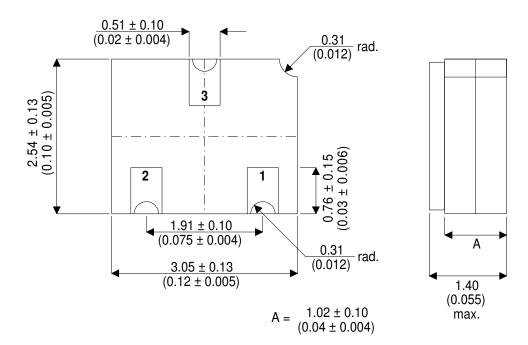
(1) Pulse Width \leq 300us, $\delta \leq 2\%$

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MECHANICAL DATA

Dimensions in mm (inches)



LCC1

Underside View

Pad 1 - Base

Pad 2 - Emitter

Pad 3 - Collector

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